# **MBR3100**

Preferred Device

# **Axial Lead Rectifier**

This device employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

#### **Features**

- Low Reverse Current
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency
- Highly Stable Oxide Passivated Junction
- Guard-ring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- High Surge Capacity
- Pb-Free Packages are Available\*

#### **Mechanical Characteristics:**

- Case: Epoxy, Molded
- Weight: 1.1 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Polarity: Cathode indicated by Polarity Band

### **MAXIMUM RATINGS**

Rating	Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	٧
Average Rectified Forward Current $T_A = 100^{\circ}C$ ( $R_{\theta JA} = 28^{\circ}C/W$ , Refer to P.C. Board Mounting, Note 3)	I <sub>O</sub>	3.0	Α
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	150	Α
Operating and Storage Junction Temperature Range (Note 1) (Reverse Voltage Applied)	T <sub>J</sub> , T <sub>stg</sub>	-65 to +175	°C
Voltage Rate of Change (Rated V <sub>R</sub> )	dv/dt	10	V/ns

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



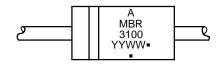
# ON Semiconductor®

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# SCHOTTKY BARRIER RECTIFIER 3.0 AMPERES, 100 VOLTS



### MARKING DIAGRAM



A = Assembly Location

YY = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MBR3100	Axial Lead	500 Units / Bag
MBR3100G	Axial Lead (Pb-Free)	500 Units / Bag
MBR3100RL	Axial Lead	1500/Tape & Reel
MBR3100RLG	Axial Lead (Pb-Free)	1500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**Preferred** devices are recommended choices for future use and best overall value.

<sup>1.</sup> The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (see Note 3, Mounting Method 3)	$R_{\theta JA}$	28	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>L</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) ( $i_F = 3.0 \text{ Amps}, T_L = 25^{\circ}\text{C}$ ) ( $i_F = 3.0 \text{ Amps}, T_L = 100^{\circ}\text{C}$ )	V <sub>F</sub>	0.79 0.69	V
Maximum Instantaneous Reverse Current @ Rated dc Voltage (Note 2) $ T_L = 25^{\circ}C \\ T_L = 100^{\circ}C $	i <sub>R</sub>	0.6 20	mA

<sup>2.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle = 2.0%.

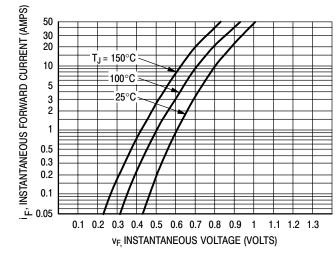


Figure 1. Typical Forward Voltage

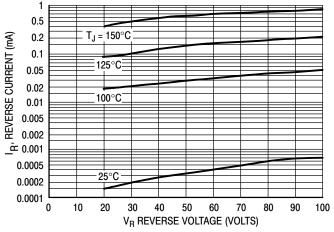


Figure 2. Typical Reverse Current\*

\*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if  $V_R$  is sufficient below rated  $V_R$ .

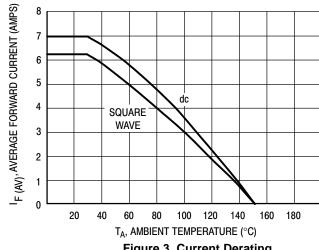


Figure 3. Current Derating (Mounting Method #3 per Note 3)

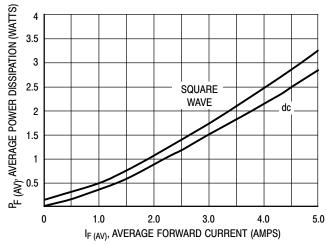


Figure 4. Power Dissipation

# **MBR3100**

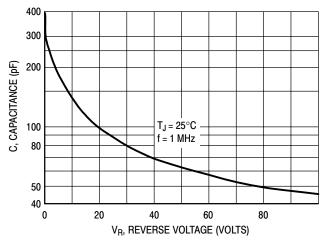


Figure 5. Typical Capacitance

## NOTE 3 — MOUNTING DATA

Data shown for thermal resistance junction—to—ambient  $(R_{\theta JA})$  for the mountings shown is to be used as typical guideline values for preliminary engineering, or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR  $R_{\theta \text{JA}}$  IN STILL AIR

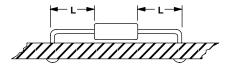
Mounting	Lead Length, L (in)				
Method	1/8	1/4	1/2	3/4	$R_{\theta JA}$
1	50	51	53	55	°C/W
2	58	59	61	63	°C/W
3	28			°C/W	

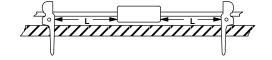
# **Mounting Method 1**

P.C. Board where available copper surface is small.

# **Mounting Method 2**

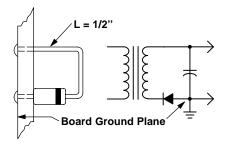
Vector Push-In Terminals T-28

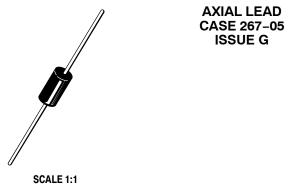




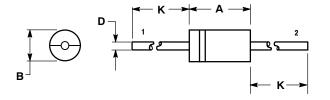
## **Mounting Method 3**

P.C. Board with 2–1/2" X 2–1/2" copper surface.





**DATE 06/06/2000** 



- NOTES:

  1. DIMENSIONS AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. 267-04 OBSOLETE, NEW STANDARD 267-05.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.287	0.374	7.30	9.50
В	0.189	0.209	4.80	5.30
D	0.047	0.051	1.20	1.30
K	1.000		25 40	

STYLE 2: NO POLARITY STYLE 1: PIN 1. CATHODE (POLARITY BAND) 2. ANODE

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